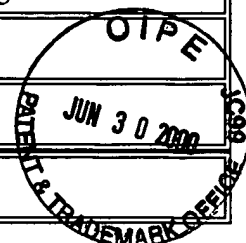


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### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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_____	AB					
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_____	AD					
_____	AE					

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Document No.	Date	Country	Translation (Yes or No)
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